

/ Descriptions

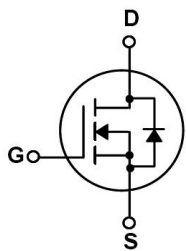
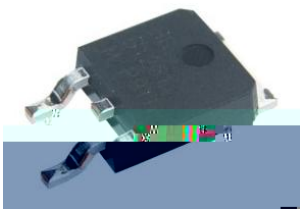
TO-252 N-MOS 60V N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

High U_{GS}/U_{DS} ratio, low $r_{DS(on)}$, low Q_g , fast switching.
Low gate charge, low cr_{ss} , fast switching.

/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



PIN 1 χ G

PIN 2 χ D

PIN 3 χ S

PIN 4 χ D

/ h_{FE} Classifications & Marking

See Marking Instructions.

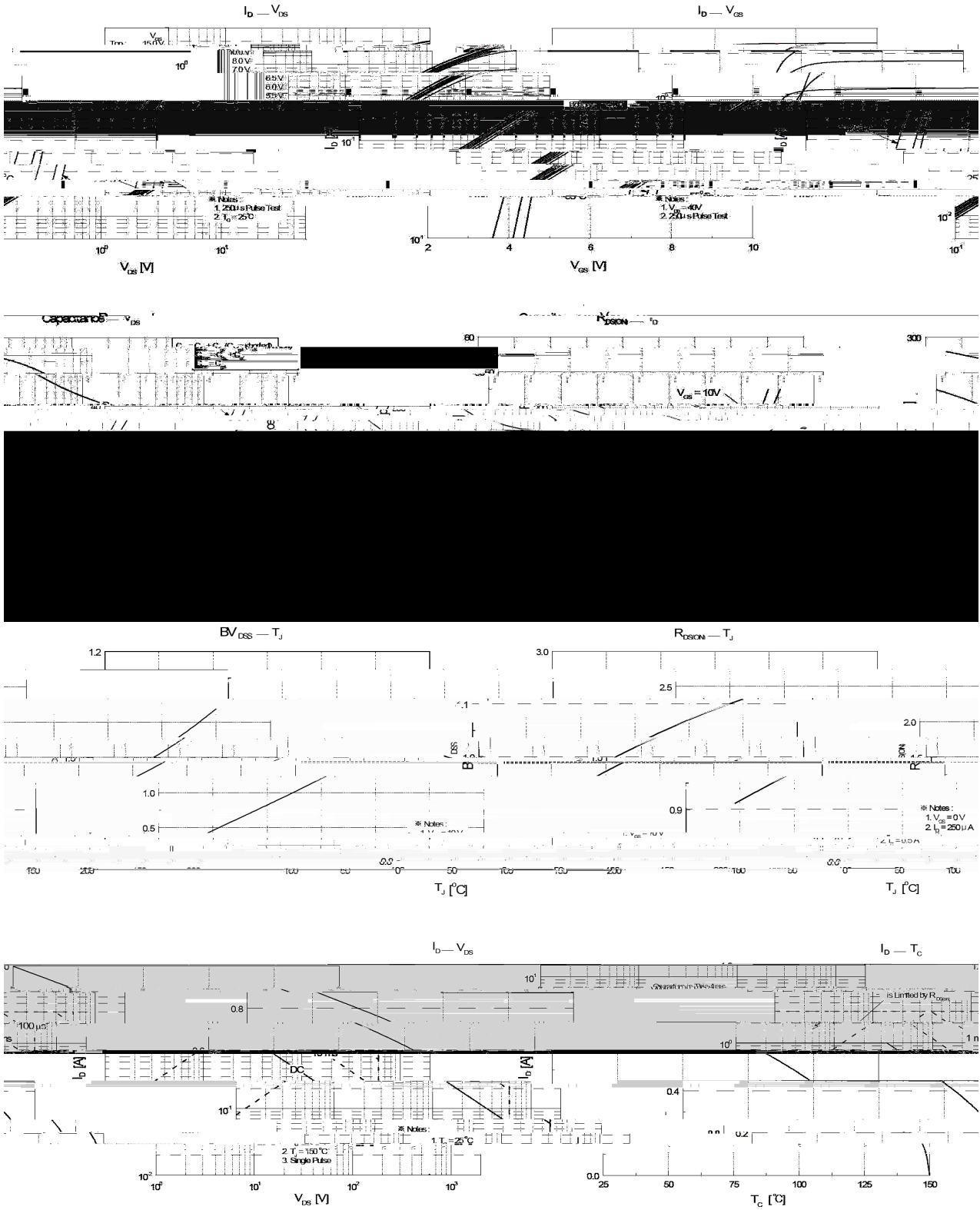
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_c=25)$	1.0	A
Drain Current	$I_D(T_c=100)$	0.6	A
Drain Current - Pulsed	I_{DM}	3.0	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	50	mJ
Repetitive Avalanche Energy	E_{AR}	2.8	mJ
Avalanche Current	I_{AR}	1.0	A
Power Dissipation	$P_D(T_c=25)$	30	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250$ A	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$ $V_{GS}=0V$			10	A
		$V_{DS}=480V$ $T_C=125$			100	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250$ A	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=0.5A$		9.7	12	
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=0.5A$		0.97		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		155	200	pF
Output Capacitance	C_{oss}			20	26	pF
Reverse Transfer Capacitance	C_{rss}			3.0	4.0	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=1.2A$ $R_G=50$		10	30	ns
Turn-On Rise Time	t_r			20	50	ns
Turn-Off Delay Time	$t_{d(off)}$			16	45	ns
Turn-Off Fall Time	t_f			25	60	ns

/ Electrical Characteristic Curve



/ Package Dimensions

